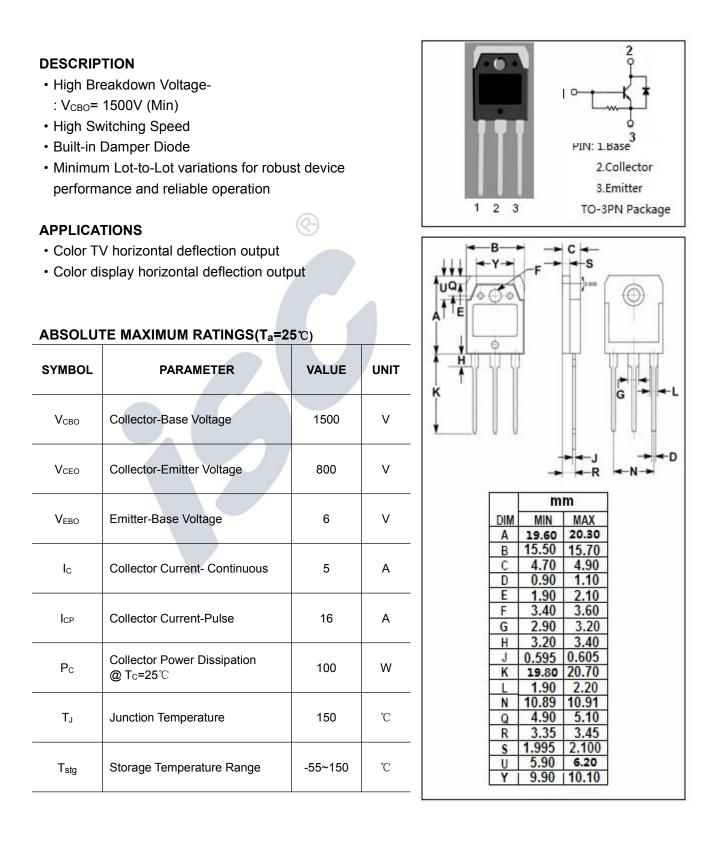


isc Silicon NPN Power Transistor

2SD1709



isc website: <u>www.iscsemi.com</u>



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ELECTRICAL CHARACTERISTICS

$T_{c}\text{=}25^{\circ}\!\!\!C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO} (SUS)	Collector-Emitter Sustaining Voltage	I _C = 50mA; I _B = 0	800			V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 4.5A; I _B = 2A			5.0	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 4.5A; I _B = 2Α			1.5	V
І _{сво}	Collector Cutoff Current	V _{CB} = 800V ; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V ; I _C = 0	40		130	mA
h _{FE-1}	DC Current Gain	I _C = 0.5A ; V _{CE} = 5V	8			
t _f	Fall Time	I _C = 4A , I _{B1} = 0.8A ; I _{B2} = 1.6A P _W =20 μ s; Duty Cycle≤1%			0.5	μ S



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